

AZ P4110 – run sheet

Merck KGaA (AZ Electronic Materials)

nanyte.com/photoresists/az-p4110 · last updated 2026-09-13

Thickness: 1–3 μm

Softbake: 95–115 °C

Exposure dose – dose by film thickness · Suss MA-200
mask aligner

Film thickness	Dose
1.5 μm	90 mJ/cm^2
3.5 μm	135 mJ/cm^2
12 μm	800 mJ/cm^2

Develop: Developer AZ 400K at 1:4, or at 1:3 / AZ 421K
(unbuffered) for films above 12 μm ; AZ Developer 1:1 where
aluminium must not be etched; AZ 340 is also listed · Dilution
AZ 400K 1:4 for better selectivity on thinner films, 1:3 for
films above 12 μm ; AZ Developer 1:1 · Method spray or immersion

Hardbake: 100–110 °C